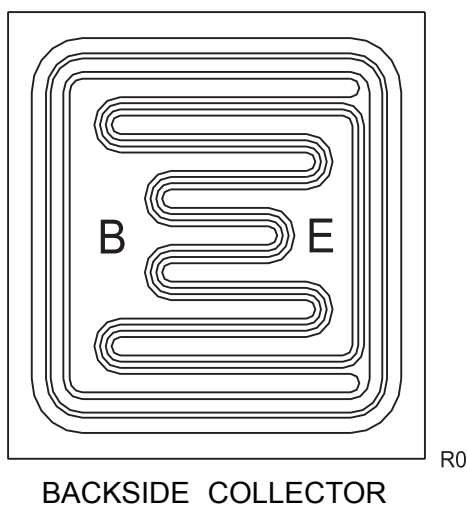


**PROCESS DETAILS**

|                          |                    |
|--------------------------|--------------------|
| Process                  | EPITAXIAL BASE     |
| Die Size                 | 66 X 66 MILS       |
| Die Thickness            | 12.5 ± 1.0 MILS    |
| Base Bonding Pad Area    | 12 X 24 MILS       |
| Emitter Bonding Pad Area | 11 X 14 MILS       |
| Top Side Metalization    | Al - 50,000Å       |
| Back Side Metalization   | Cr/Ni/Ag - 16,000Å |

**GEOMETRY****GROSS DIE PER 4 INCH WAFER**

2,630

**PRINCIPAL DEVICE TYPES**

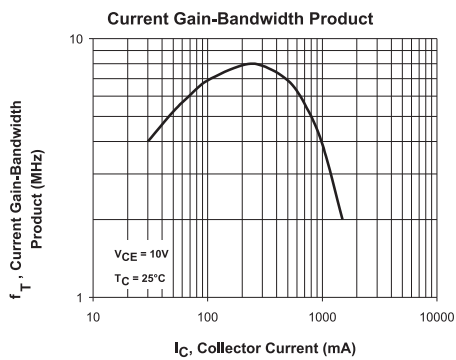
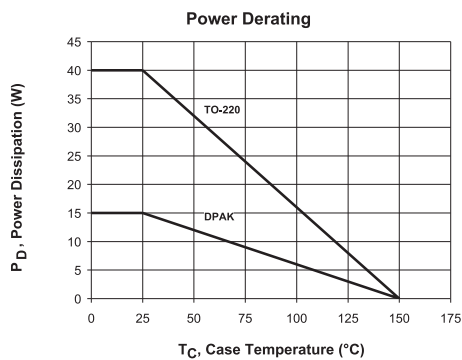
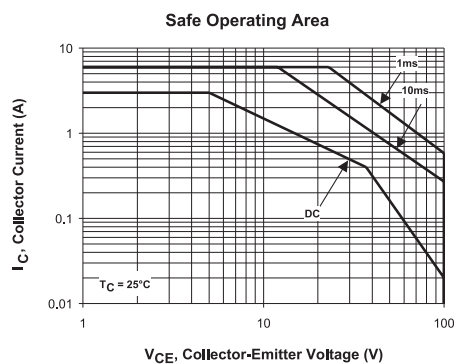
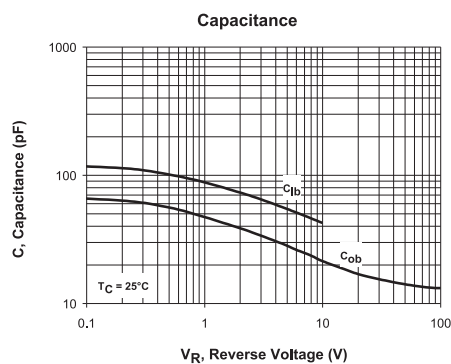
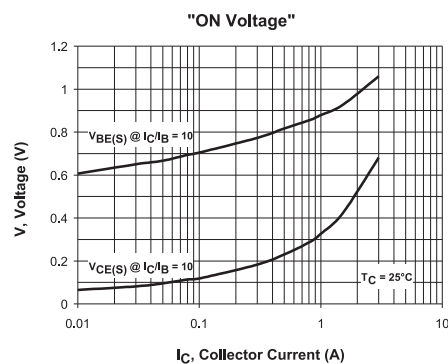
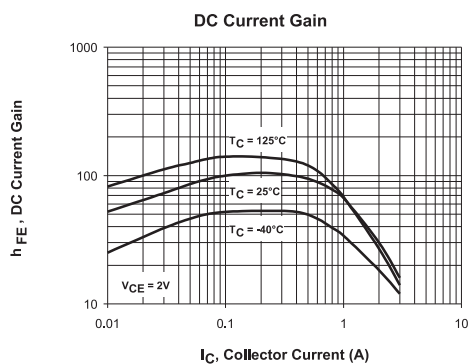
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